MSKSEMI 美森科













ESD

TSS

MOV

GDT

PIFD

RCLAMP0502BATCT-MS

Product specification





Features

- 45 Watts peak pulse power (tp = 8/20µs)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.7 pF typ.)
- Protection two data lines
- IEC 61000-4-2 ±20kV contact ±15kV air
- IEC 61000-4-4 (EFT) 40A(5/50ns)
- IEC 61000-4-5 (Lightning) 3.5A (8/20μs)

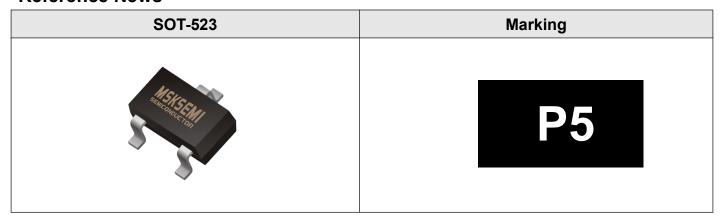
Mechanical Data

- SOT-523 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

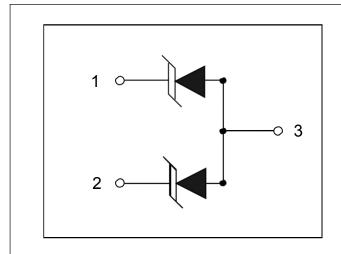
Applications

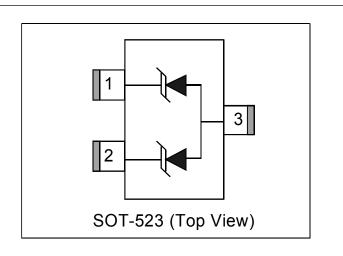
- Dataline
- Automatic Teller Machines
- Net works
- Power line

Reference News



Schematic & PIN Configuration







Absolute Maximum Rating

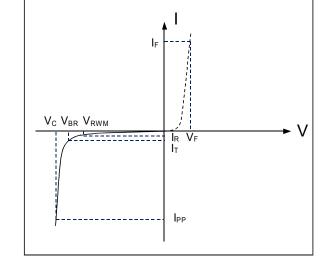
| Rating | Symbol | Value | Units |
|---|------------------|----------------|---------------|
| Peak Pulse Power (t _p =8/20µs) | P _{PP} | 45 | Watts |
| Peak Pulse Current (t _p =8/20μs)(note1) | I _{pp} | 3.5 | А |
| ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2 (Contact) | V _{ESD} | 20 15 | kV |
| Lead SolderingTemperature | TL | 260(10seconds) | ${\mathbb C}$ |
| JunctionTemperature | TJ | -55 to + 125 | ${\mathbb C}$ |
| StorageTemperature | T _{stg} | -55 to + 125 | ${\mathbb C}$ |

Electrical Characteristics

| Parameter | Symbol | Conditions | Min | Typical | Max | Units |
|--------------------------|------------------|-------------------------------------|-----|---------|-----|-------|
| Reverse Stand-OffVoltage | V _{RWM} | | | | 5 | V |
| Reverse BreakdownVoltage | V_{BR} | I _T =1mA | 6 | | | V |
| Reverse LeakageCurrent | I _R | V _{RWM} =5V,T=25℃ | | | 1 | μA |
| Peak Pulse Current | I _{PP} | tp =8/20μs | | | 3.5 | А |
| Clamping Voltage | Vc | I_{PP} =3.5A, t_p =8/20 μ s | | | 25 | V |
| JunctionCapacitance | C _j | $V_R = 0V, f=1MHz$ | | 0.7 | 0.8 | pF |

Electrical Parameters (TA = 25°C unless otherwisenoted)

| Symbo | Parameter |
|-------------|--|
| I PP | Maximum Reverse Peak Pulse Current |
| Vc | Clamping Voltage @ IPP |
| VRWM | Working Peak Reverse Voltage |
| lR | Maximum Reverse Leakage Current @ VRWM |
| VBR | Breakdown Voltage @ I⊤ |
| lτ | Test Current |
| | |
| | |



Note: 8/20µs pulsewaveform.



TypicalCharacteristics

Figure 1: Peak Pulse Power vs. Pulse Time

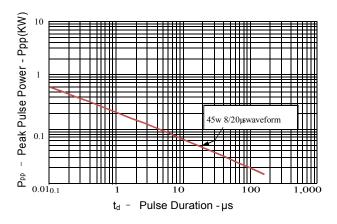


Figure 2: Power Derating Curve

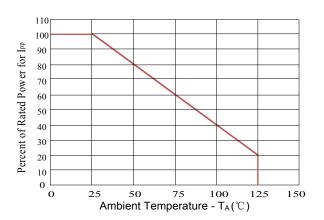


Figure3: Pulse Waveform

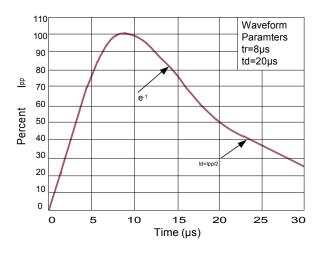
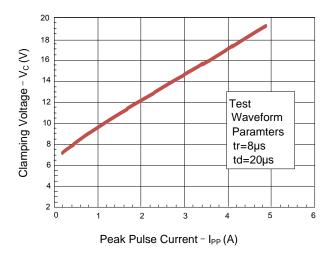
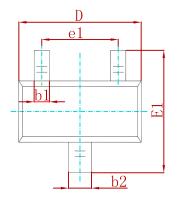


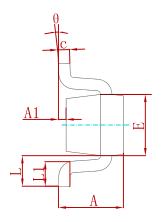
Figure 4: Clamping Voltage vs.lpp

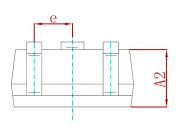




PACKAGEMECHANICALDATA

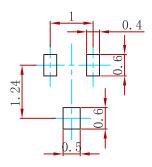






| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| Symbol | Min. | Max. | Min. | Max. |
| Α | 0.700 | 0.900 | 0.028 | 0.035 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.700 | 0.800 | 0.028 | 0.031 |
| b1 | 0.150 | 0.250 | 0.006 | 0.010 |
| b2 | 0.250 | 0.350 | 0.010 | 0.014 |
| С | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 1.500 | 1.700 | 0.059 | 0.067 |
| E | 0.700 | 0.900 | 0.028 | 0.035 |
| E1 | 1.450 | 1.750 | 0.057 | 0.069 |
| е | 0.500 TYP. | | 0.020 TYP. | |
| e1 | 0.900 | 1.100 | 0.035 | 0.043 |
| L | 0.400 REF. | | 0.016 REF. | |
| L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

Order information

| Orderable Device | Package | Packing Option |
|--------------------|---------|----------------|
| RCLAMP0502BATCT-MS | SOT-523 | 3000PCS |

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